

TOSHIBA**2SC5000**

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE

2SC5000

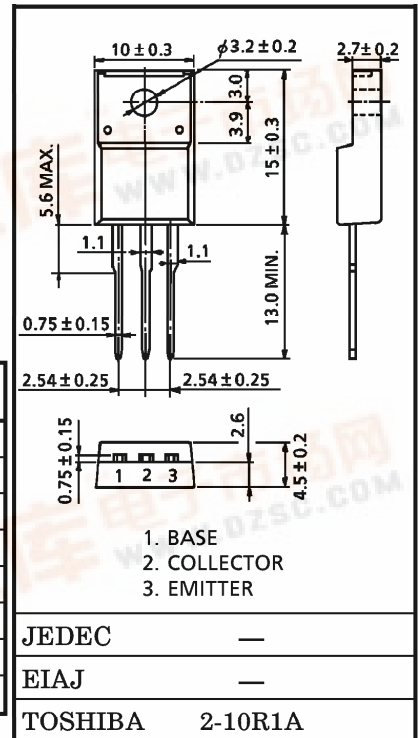
POWER AMPLIFIER APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.4\text{ V (Max.)}$ ($I_C = 5\text{ A}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	10	A
Base Current	I_B	1	A
Collector Power Dissipation	P_C	25	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 70\text{ V}, I_E = 0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	50	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 1\text{ V}, I_C = 1\text{ A}$	120	—	400	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C = 5\text{ A}, I_B = 0.25\text{ A}$	—	0.19	V
	Base-Emitter	$V_{BE(sat)}$	$I_C = 5\text{ A}, I_B = 0.25\text{ A}$	—	0.96	
Transition Frequency	f_T	$V_{CE} = 1\text{ V}, I_C = 1\text{ A}$	—	90	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	90	—	pF

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